

(b) Amendments to the Claims:

Please amend claim 1 as follows. A detailed listing of the claims follows which replaces all earlier listings:

1. (Currently Amended) A method for making a piezoelectric element comprising a piezoelectric film formed on a substrate by a gas deposition technique, the method comprising the steps of:

ejecting ultra-fine particles of a piezoelectric material having a perovskite structure from an ejecting device toward the substrate; and

applying a potential difference (a) between the ejecting device and the substrate or (b) between an electrode in the vicinity of the ejecting device and the substrate, to apply an electric field to the ultra-fine particles traveling to the substrate sufficient to polarize and macroscopically orient the particles to form a deposited film with dipoles oriented in the direction of the electric field, wherein the potential difference is provided by an external power source and a current-limiting circuit is provided on the external power source or between the external power source and the ejecting device to prevent flow of excess current and eliminate electrical discharge when the ultra-fine particles are ejected.

2. (Original) A method for making a piezoelectric element according to Claim 1, wherein the electric field applied has an intensity in the range of 0.5 to 3 kV/mm.

3. (Original) A method for making a piezoelectric element according to Claim 2, wherein the electric field applied has an intensity in the range of 1 to 2 kV/mm.

4. (Original) A method for making a piezoelectric element according to
Claim 1, wherein the substrate comprises a metal.

5. (Original) A method for making a piezoelectric element according to
Claim 1, wherein the substrate comprises a resin.